

9097250 TOSHIBA (DISCRETE/OPTO)

67C 09303 D T-01-09

**1S2092**

Silicon Epitaxial Planar Type

Diode

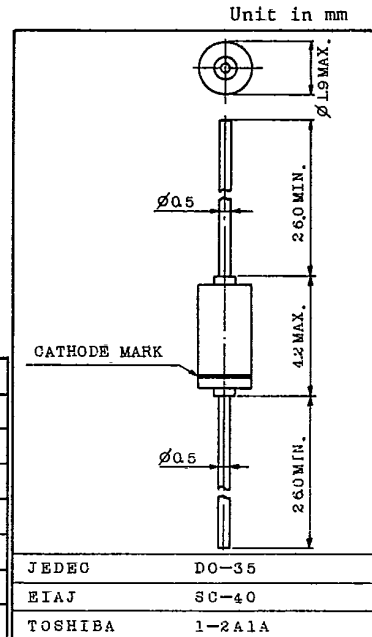
## GENERAL PURPOSE DETECTOR AND RECTIFIER APPLICATIONS

## FEATURES:

- High Maximum (Peak) Reverse Voltage :  $V_{RM}=125V$
- Small Total Capacitance :  $C_T=0.7pF$  (Typ.)
- Fast Reverse Recovery Time :  $t_{rr}=2ns$  (Typ.)

MAXIMUM RATINGS ( $T_a=25^\circ C$ )

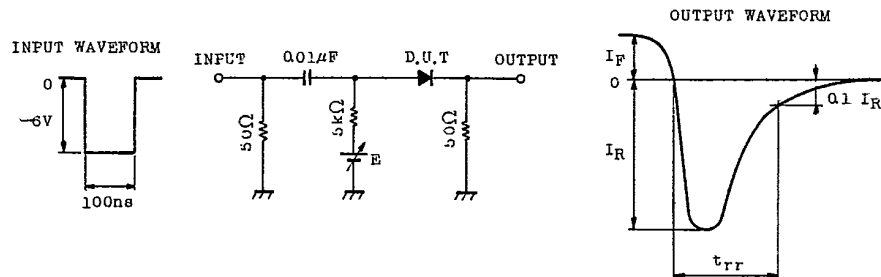
CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum(Peak) Reverse Voltage	$V_{RM}$	125	V
Reverse Voltage	$V_R$	100	V
Maximum(Peak) Forward Current	$I_{FM}$	90	mA
Average Forward Current	$I_O$	30	mA
Surge Current (1 sec)	$I_{FSM}$	300	mA
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55 ~ 150	$^\circ C$



Weight : 0.14g

ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Current	$I_F$	$V_F=1.0V$	4.0	-	-	mA
Reverse Current	$I_R$	$V_R=100V$	-	-	1.2	$\mu A$
Total Capacitance	$C_T$	$V_R=0, f=1MHz$	-	0.7	3.0	pF
Reverse Recovery Time	$t_{rr}$	$I_F=10mA$ (Fig.)	-	2	100	ns

Fig. :  $t_{rr}$  TEST CIRCUIT

TOSHIBA CORPORATION

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